

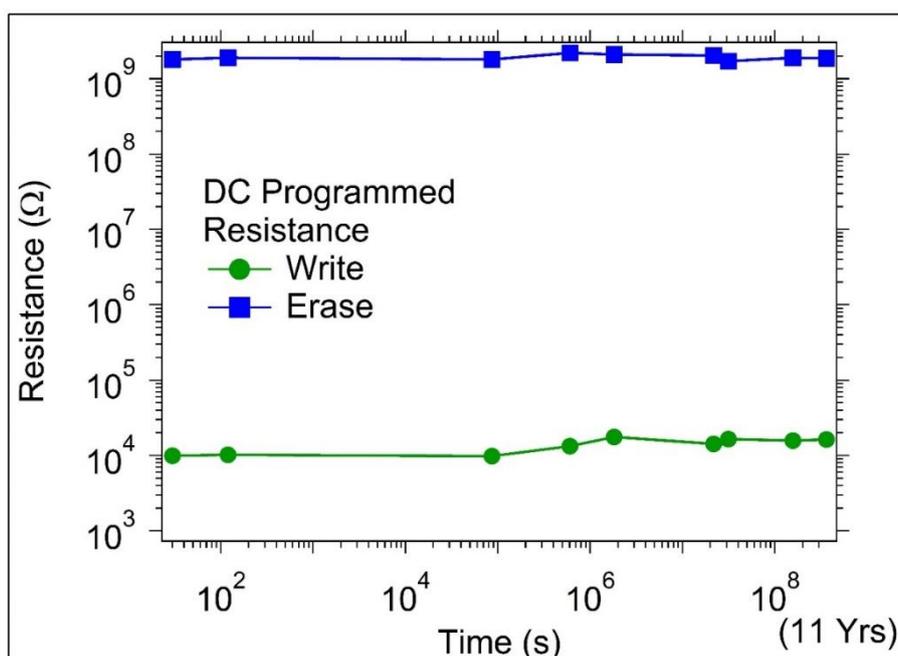
Supplemental Material

# Comparison of the Electrical Response of Cu and Ag Ion-Conducting SDC Memristors Over the Temperature Range 6 K to 300 K

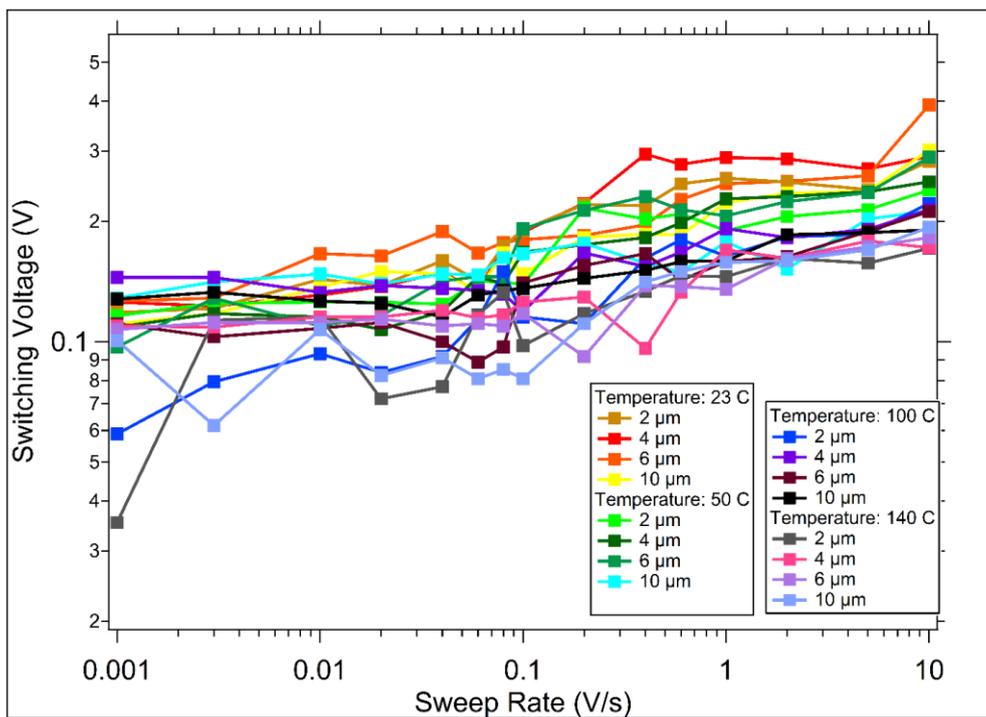
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**Figure 1.** Data retention of Ag-based SDC memristors over 11 years. 20 devices are in a written state and 20 devices in an erased state. Measurements are made periodically to investigate state drift.



**Figure 2.** Ag-based device switching voltage as a function of DC sweep rate over the temperature range of ~300 K to 413 K.